

Title (en)  
TRANSISTOR WITH INTERDIGITAL ELECTRODES, COMPRISING A GATE TERMINAL CONNECTED BY A PLURALITY OF VERTICAL VIAS TO THE GATE ELECTRODES

Title (de)  
TRANSISTOR MIT INTERDIGITALELEKTRODEN MIT EINEM GATE-ANSCHLUSS, DER ÜBER MEHRERE VERTIKALE DURCHKONTAKTIERUNGEN MIT DEN GATE-ELEKTRODEN VERBUNDEN IST

Title (fr)  
TRANSISTOR A ELECTRODES INTERDIGITEES, COMPRENANT UN TERMINAL DE GRILLE CONNECTE PAR UNE PLURALITE DE VIAS VERTICAUX AUX ELECTRODES DE GRILLE

Publication  
**EP 4173033 A1 20230503 (FR)**

Application  
**EP 21737725 A 20210615**

Priority  
• FR 2006863 A 20200630  
• FR 2021051069 W 20210615

Abstract (en)  
[origin: WO2022003265A1] The invention relates to a field-effect transistor (100) having an interdigital structure and comprising: several elementary transistor cells (50) arranged in parallel, each elementary cell comprising a source electrode (1), a drain electrode (3) and a gate electrode (2) interposed between the source and drain electrodes, a source terminal (10) and a drain terminal (30) respectively connected to the source electrodes (1) and to the drain electrodes (3) of the elementary cells (50), a gate terminal (20) connected to the gate electrodes (2) of the elementary cells. The field-effect transistor (100) comprises only vertical conductive vias for connecting the gate electrodes to the gate terminal, and the gate terminal (20) is arranged vertically in line with all or part of the elementary cells (50).

IPC 8 full level  
**H01L 23/48** (2006.01); **H01L 23/482** (2006.01); **H01L 23/522** (2006.01); **H01L 29/423** (2006.01)

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Citation (search report)  
See references of WO 2022003265A1

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DOCDB simple family (publication)  
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